

AMENDMENTS TO THE SPECIFICATION:

Please delete the paragraph bridging pages 15 and 16 of Applicant's specification (that is, page 15, line 24 through page 16, line 15) and substitute therefor the following new paragraph:

--As mentioned previously, in order to conduct etching treatment recently applied with good accuracy, it is essential that RF bias is applied to the substrate stage 10 and the substrate 1 is adsorbed by electrostatic adsorption. According to the electrostatic adsorption, a direct voltage is applied between the substrate 1 and the substrate stage 10 to store the charge between the substrate 1 and the substrate stage 10, and thus the substrate 1 is adsorbed. In Fig. 2, reference character 3 denotes a DC power supply. In order to remove the adsorption after the etching treatment, the voltage is cut. But, since the stored charge is not discharged immediately, it is necessary to connect the substrate 1 and the substrate stage 10 to earth 15. The earth from the substrate 1 in the case of electrostatic adsorption is taken from the inner wall surface while forming an earth line 16 via plasma 4, so that it is necessary to discharge for destaticization for a time necessary to discharge the stored charge.--